

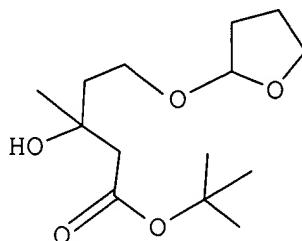
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Response dated November 10, 2004
Reply to Office Action of August 10, 2004

AMENDMENTS TO THE CLAIMS:

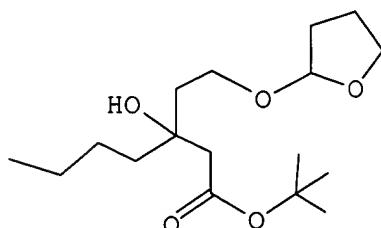
This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (currently amended): A chemically amplified resist composition comprising a base resin reacting in the presence of an acid, a photo acid generator generating an acid upon exposure, and a compound having the combination of an acetal moiety and a site which is eliminated by an acid in its molecule, wherein said compound is represented by the formula:



or



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Claim 2 (original): The chemically amplified resist composition of claim 1, wherein said compound has the acetal moiety and the site eliminated by an acid at locations such that a final product containing a ring structure can be produced through reactions in the presence of the acid.

Claim 3 (canceled)

Claim 4 (previously presented): The chemically amplified resist composition of claim 1, wherein said base polymer is a homopolymer of an acrylate or methacrylate monomer or a copolymer of two or more of such monomers, a polymer of cycloolefin monomer, or a hybrid polymer of an acrylate or methacrylate monomer and a cycloolefin monomer.

Claim 5 (previously presented): The chemically amplified resist composition of claim 2, wherein said base polymer is a homopolymer of an acrylate or methacrylate monomer or a copolymer of two or more of such monomers, a polymer of cycloolefin monomer, or a hybrid polymer of an acrylate or methacrylate monomer and a cycloolefin monomer.

Claim 6 (original): The chemically amplified resist composition of claim 1, wherein said base resin is a copolymer of 2-methyladamantyl methacrylate and gamma-butyrolactone methacrylate.

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Claim 7 (original): The chemically amplified resist composition of claim 2, wherein said base resin is a copolymer of 2-methyladamantyl methacrylate and gamma-butyrolactone methacrylate.

Claims 8-19 (canceled)

Claim 20 (original): A method for forming a patterned film by applying a resist material to a film provided on the surface of a substrate, to form a resist layer, pre-baking the resist layer, selectively exposing the pre-baked resist layer to a radiation, post-baking the exposed resist layer, developing the post-baked resist layer to form a resist pattern, and patterning the film underlying the resist pattern by the use of the resist pattern as a mask, wherein the chemically amplified resist composition of claim 1 is used as the resist material.

Claim 21 (canceled)

Claim 22 (original): The method of claim 20, wherein said radiation is an excimer laser beam, X-rays, or an electron beam.

Claim 23 (canceled)

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Claim 24 (original): The method of claim 20, wherein said radiation is an ArF excimer laser beam or vacuum ultraviolet light having a shorter wavelength.

Claim 25 (canceled)

Claim 26 (new): A chemically amplified resist composition comprising a base resin reacting in the presence of an acid, a photo acid generator generating an acid upon exposure, wherein the base resin has a repeating unit having the combination of an acetal moiety and a site which is eliminated by an acid.